

# Dual Series Schottky Barrier Diodes

## BAT54SL

These Schottky barrier diodes are designed for high speed switching applications, circuit protection, and voltage clamping. Extremely low forward voltage reduces conduction loss. Miniature surface mount package is excellent for hand held and portable applications where space is limited.

### Features

- Extremely Fast Switching Speed
- Low Forward Voltage – 0.35 V (Typ) @  $I_F = 10 \text{ mA}$
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

| Rating   | Symbol    | Value       | Unit                       |
|--|-----------|-------------|----------------------------|
| Reverse Voltage  | $V_R$     | 30          | V                          |
| Forward Power Dissipation<br>@ $T_A = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$ | $P_F$     | 225<br>1.8  | mW<br>mW/ $^\circ\text{C}$ |
| Forward Current (DC)   | $I_F$     | 200 Max     | mA                         |
| Non-Repetitive Peak Forward Current<br>$t_p < 10 \text{ msec}$<br>Square pulse = 1 sec     | $I_{FSM}$ | 600<br>1.0  | mA<br>A                    |
| Repetitive Peak Forward Current<br>Pulse Wave = 1 sec,<br>Duty Cycle = 66%                 | $I_{FRM}$ | 300         | mA                         |
| Junction Temperature   | $T_J$     | -55 to 150  | $^\circ\text{C}$           |
| Storage Temperature Range  | $T_{stg}$ | -55 to +150 | $^\circ\text{C}$           |

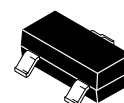
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



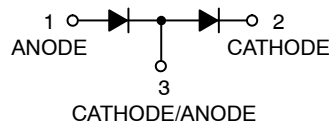
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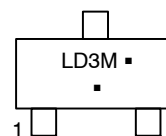
## 30 VOLT DUAL SCHOTTKY BARRIER DIODES



SOT-23  
CASE 318  
STYLE 11



### MARKING DIAGRAM



LD3 = Device Code  
M = Date Code\*  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

### ORDERING INFORMATION

| Device      | Package             | Shipping†           |
|-------------|---------------------|---------------------|
| BAT54SLT1G  | SOT-23<br>(Pb-Free) | 3,000 / Tape & Reel |
| SBAT54SLT1G | SOT-23<br>(Pb-Free) | 3,000 / Tape & Reel |

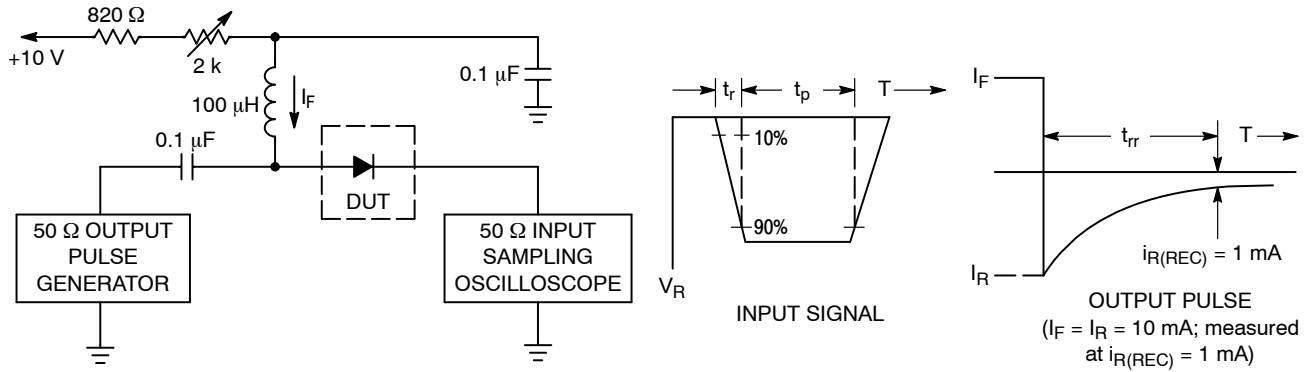
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# BAT54SL

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted) (EACH DIODE)

| Characteristic  | Symbol      | Min | Typ                                  | Max                                  | Unit             |
|---|-------------|-----|--------------------------------------|--------------------------------------|------------------|
| Reverse Breakdown Voltage<br>( $I_R = 10 \mu\text{A}$ )   | $V_{(BR)R}$ | 30  | -                                    | -                                    | V                |
| Total Capacitance<br>( $V_R = 1.0 \text{ V}$ , $f = 1.0 \text{ MHz}$ )  | $C_T$       | -   | 7.6                                  | 10                                   | pF               |
| Reverse Leakage<br>( $V_R = 25 \text{ V}$ )   | $I_R$       | -   | 0.15                                 | 2.0                                  | $\mu\text{A}$ dc |
| Forward Voltage<br>( $I_F = 0.1 \text{ mA}$ )<br>( $I_F = 1.0 \text{ mA}$ )<br>( $I_F = 10 \text{ mA}$ )<br>( $I_F = 30 \text{ mA}$ )<br>( $I_F = 100 \text{ mA}$ ) | $V_F$       | -   | 0.22<br>0.29<br>0.35<br>0.41<br>0.52 | 0.24<br>0.32<br>0.40<br>0.50<br>0.80 | V                |
| Reverse Recovery Time<br>( $I_F = I_R = 10 \text{ mA}$ dc, $I_{R(\text{REC})} = 1.0 \text{ mA}$ dc, Figure 1)   | $t_{rr}$    | -   | -                                    | 5.0                                  | ns               |

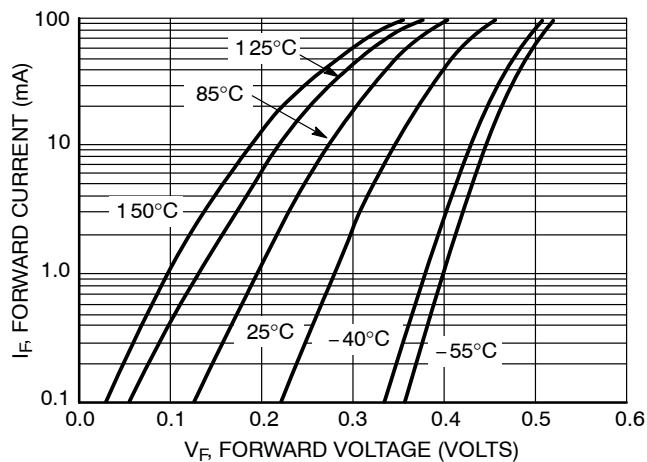
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



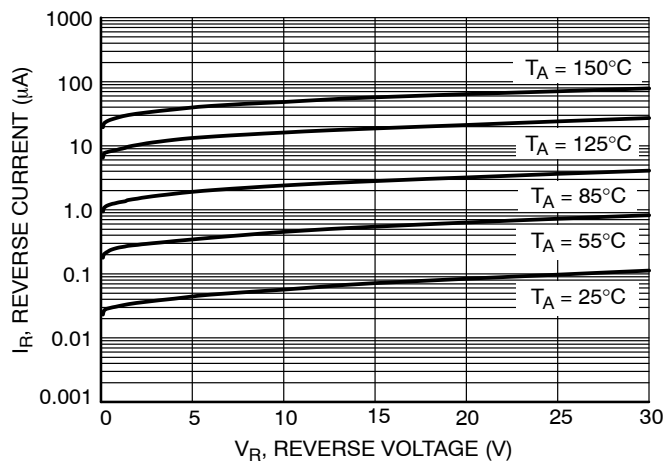
- Notes:
1. A 2.0 k $\Omega$  variable resistor adjusted for a Forward Current ( $I_F$ ) of 10 mA.
  2. Input pulse is adjusted so  $I_{R(\text{peak})}$  is equal to 10 mA.
  3.  $t_p \gg t_{rr}$

**Figure 1. Recovery Time Equivalent Test Circuit**

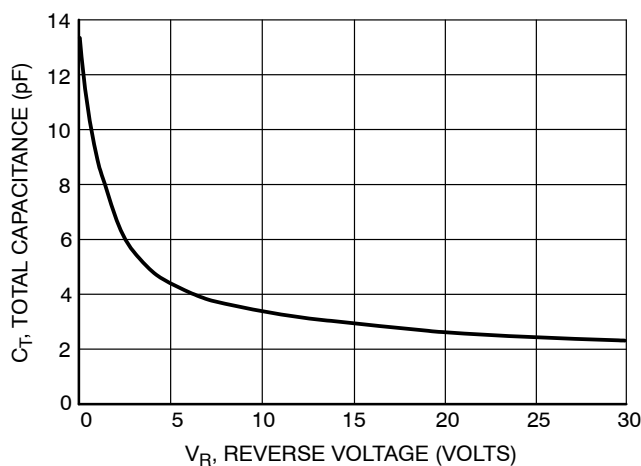
# BAT54SL



**Figure 2. Forward Voltage**



**Figure 3. Leakage Current**



**Figure 4. Total Capacitance**

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

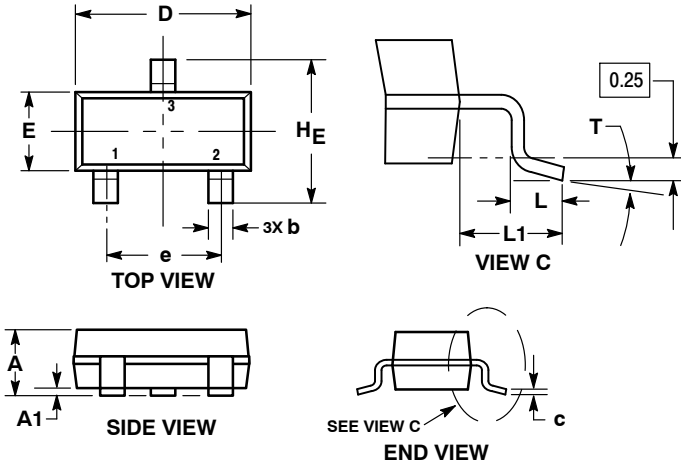
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**SOT-23 (TO-236)**  
CASE 318-08  
ISSUE AS

DATE 30 JAN 2018

SCALE 4:1

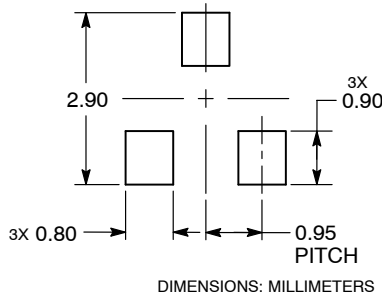


**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

| DIM | MILLIMETERS |      |      | INCHES |       |       |
|-----|-------------|------|------|--------|-------|-------|
|     | MIN         | NOM  | MAX  | MIN    | NOM   | MAX   |
| A   | 0.89        | 1.00 | 1.11 | 0.035  | 0.039 | 0.044 |
| A1  | 0.01        | 0.06 | 0.10 | 0.000  | 0.002 | 0.004 |
| b   | 0.37        | 0.44 | 0.50 | 0.015  | 0.017 | 0.020 |
| c   | 0.08        | 0.14 | 0.20 | 0.003  | 0.006 | 0.008 |
| D   | 2.80        | 2.90 | 3.04 | 0.110  | 0.114 | 0.120 |
| E   | 1.20        | 1.30 | 1.40 | 0.047  | 0.051 | 0.055 |
| e   | 1.78        | 1.90 | 2.04 | 0.070  | 0.075 | 0.080 |
| L   | 0.30        | 0.43 | 0.55 | 0.012  | 0.017 | 0.022 |
| L1  | 0.35        | 0.54 | 0.69 | 0.014  | 0.021 | 0.027 |
| HE  | 2.10        | 2.40 | 2.64 | 0.083  | 0.094 | 0.104 |
| T   | 0°          | ---  | 10°  | 0°     | ---   | 10°   |

**RECOMMENDED SOLDERING FOOTPRINT**



**GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

STYLE 1 THRU 5:  
CANCELLED

STYLE 6:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

STYLE 7:  
PIN 1. EMITTER  
2. BASE  
3. COLLECTOR

STYLE 8:  
PIN 1. ANODE  
2. NO CONNECTION  
3. CATHODE

STYLE 9:  
PIN 1. ANODE  
2. ANODE  
3. CATHODE

STYLE 10:  
PIN 1. DRAIN  
2. SOURCE  
3. GATE

STYLE 11:  
PIN 1. ANODE  
2. CATHODE  
3. CATHODE-ANODE

STYLE 12:  
PIN 1. CATHODE  
2. CATHODE  
3. ANODE

STYLE 13:  
PIN 1. SOURCE  
2. DRAIN  
3. GATE

STYLE 14:  
PIN 1. CATHODE  
2. GATE  
3. ANODE

STYLE 15:  
PIN 1. GATE  
2. CATHODE  
3. ANODE

STYLE 16:  
PIN 1. ANODE  
2. CATHODE  
3. CATHODE

STYLE 17:  
PIN 1. NO CONNECTION  
2. ANODE  
3. CATHODE

STYLE 18:  
PIN 1. NO CONNECTION  
2. CATHODE  
3. ANODE

STYLE 19:  
PIN 1. CATHODE  
2. ANODE  
3. CATHODE-ANODE

STYLE 20:  
PIN 1. CATHODE  
2. ANODE  
3. GATE

STYLE 21:  
PIN 1. GATE  
2. SOURCE  
3. DRAIN

STYLE 22:  
PIN 1. RETURN  
2. OUTPUT  
3. INPUT

STYLE 23:  
PIN 1. ANODE  
2. ANODE  
3. CATHODE

STYLE 24:  
PIN 1. GATE  
2. DRAIN  
3. SOURCE

STYLE 25:  
PIN 1. ANODE  
2. CATHODE  
3. GATE

STYLE 26:  
PIN 1. CATHODE  
2. ANODE  
3. NO CONNECTION

STYLE 27:  
PIN 1. CATHODE  
2. CATHODE  
3. CATHODE

STYLE 28:  
PIN 1. ANODE  
2. ANODE  
3. ANODE

|                         |                        |  |
|-------------------------|------------------------|--|
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